

COMPLEMENTARY PAIR SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

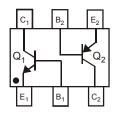
- Epitaxial Die Construction
- Two Internally Isolated NPN/PNP Transistors in One Package
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The BC847BVNQ are suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame.
 - Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.003 grams (Approximate)





Device Schematic Top View

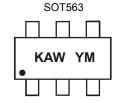
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC847BVNQ-7	Automotive	KAW	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



KAW = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Date Odde Ney												
Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	ı	J	K	L	М	N	0	Р	R	S	Т
	1	1	1	1	1	I	1		I		I	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings: NPN, BC847B Type (Q₁) (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	Ic	100	mA
Peak Pulse Collector Current (single pulse)	I _{CM}	200	mA
Peak Pulse Emitter Current (single pulse)	I _{EM}	200	mA

Maximum Ratings: PNP, BC857B Type (Q₂) (@ T_A = +25°C unless otherwise specified.)

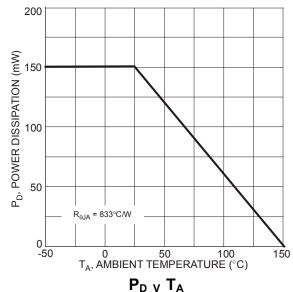
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	Ic	-100	mA
Peak Pulse Collector Current (single pulse)	I _{CM}	-200	mA
Peak Pulse Emitter Current (single pulse)	I _{EM}	-200	mA

Thermal Characteristics – Total Device (@ T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note:

Thermal Characteristics - Total Device



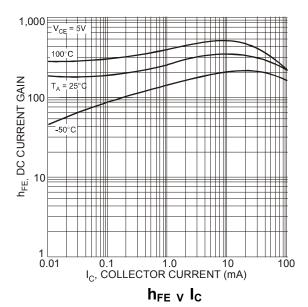
^{6.} For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

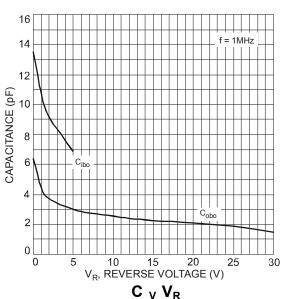


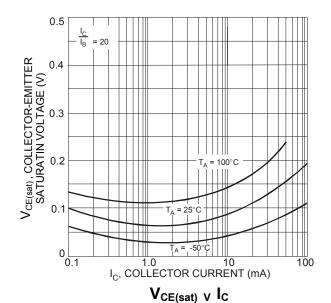
Electrical Characteristics: NPN, BC847B Type (Q₁) (@ T_A = +25°C unless otherwise specified.)

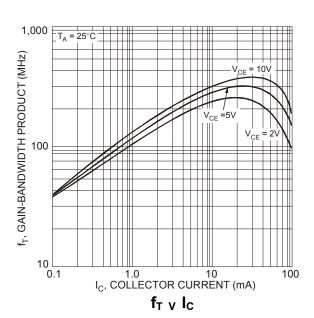
Characteristic (Note 7)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	_	-	V	$I_C = 100\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	45	-	_	V	$I_C = 10mA, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	$I_E = 100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	200	290	450	_	$V_{CE} = 5.0V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		90 200	250 600	l mv	I _C = 10mA, I _B = 0.5mA
	- (,			000		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	700 900	_	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
		580	660	700		$V_{CF} = 5.0V$, $I_{C} = 2.0$ mA
Base-Emitter Voltage	$V_{BE(on)}$	-	—	700 720	l mv	$V_{CE} = 5.0V$, $I_{C} = 2.011A$ $V_{CE} = 5.0V$, $I_{C} = 10mA$
0 1 0 10 0			_	15		V _{CB} = 30V
Collector Cut Off Current	I _{CBO}	_	_	5.0	μΑ	V _{CB} = 30V, T _A = +150°C
Transition Frequency	f _T	100	300	_	MHz	V _{CE} = 5.0V, I _C = 10mA, f = 100MHz
Collector-Base Capacitance	C _{cbo}	_	3.5	6.0	pF	V _{CB} = 10V, f = 1.0MHz

Note: 7. Short duration pulse test used to minimize self-heating effect.







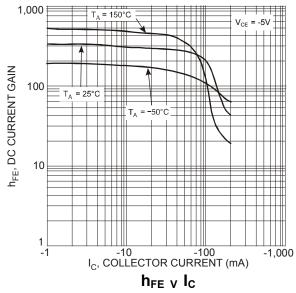


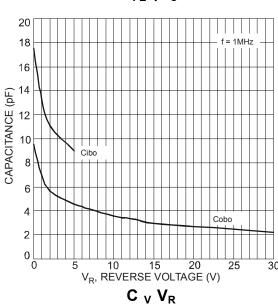


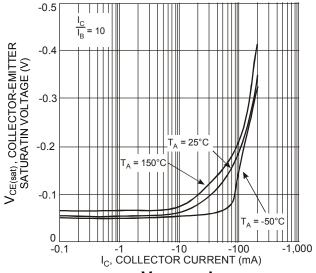
Electrical Characteristics: PNP, BC857B Type (Q₂) (@ T_A = +25°C unless otherwise specified.)

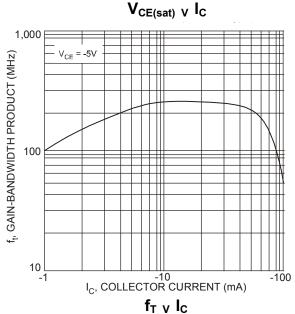
Characteristic (Note 8)	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	_		V	$I_C = -100\mu A, I_B = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	_		٧	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_		V	$I_E = -100 \mu A, I_C = 0$
DC Current Gain	h _{FE}	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	1	-75 -250	-300 -650	mV	$I_C = -10mA$, $I_B = -0.5mA$ $I_C = -100mA$, $I_B = -5.0mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}		-700 -850	— -950	mV	$I_C = -10\text{mA}, I_B = -0.5\text{mA}$ $I_C = -100\text{mA}, I_B = -5.0\text{mA}$
Base-Emitter Voltage	V _{BE(on)}	-600 —	-650 —	-750 -820	mV	V_{CE} = -5.0V, I_{C} = -2.0mA V_{CE} = -5.0V, I_{C} = -10mA
Collector Cut Off Current	I _{CBO}		-	-15 -4.0	nΑ μΑ	V _{CB} = -30V V _{CB} = -30V, T _A = +150°C
Transition Frequency	f⊤	100	200		MHz	$V_{CE} = -5.0V$, $I_{C} = -10mA$, $f = 100MHz$
Collector-Base Capacitance	C _{cbo}	_	3	4.5	pF	V _{CB} = -10V, f = 1.0MHz

Note: 8. Short duration pulse test used to minimize self-heating effect.





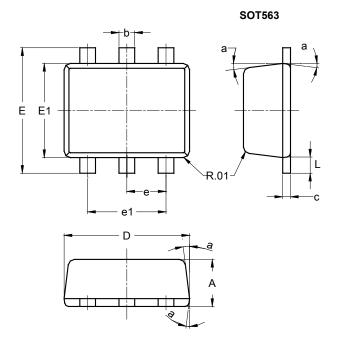






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

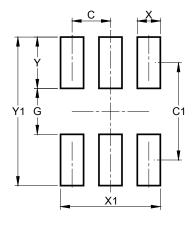


SOT563						
Dim	Min	Max	Тур			
Α	0.55	0.60	0.60			
b	0.15	0.30	0.20			
С	0.10	0.18	0.11			
D	1.50	1.70	1.60			
Е	1.55	1.70	1.60			
E1	1.10	1.25	1.20			
е			0.50			
e1	0.90	1.10	1.00			
L	0.10	0.30	0.20			
а	8°	9°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
С	0.500
C1	1.270
G	0.600
Х	0.300
X1	1.300
Υ	0.670
V1	1 940



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